

NTLLD4901NF

MOSFET – Power, Dual, N-Channel with Integrated Schottky WDFN, (3 mm x 3 mm)

30 V, High Side 11 A / Low Side 13 A

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

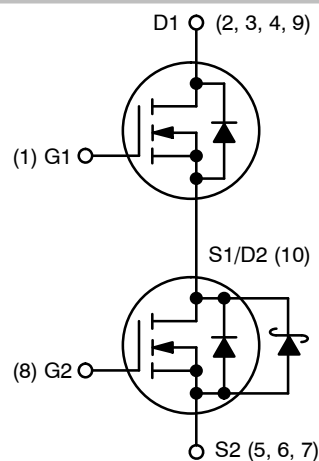
- DC-DC Converters
- System Voltage Rails
- Point of Load



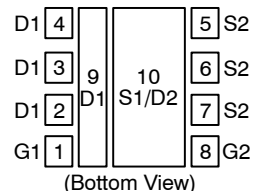
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$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
Q1 Top FET 30 V	17.4 mΩ @ 10 V	11 A
	25 mΩ @ 4.5 V	
Q2 Bottom FET 30 V	13.3 mΩ @ 10 V	13 A
	20 mΩ @ 4.5 V	



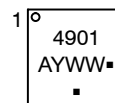
PIN CONNECTIONS



MARKING DIAGRAM



WDFN8
CASE 511BP



- 4901 = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage	Q1	V_{DSS}	30	V	
Drain-to-Source Voltage	Q2				
Gate-to-Source Voltage	Q1	V_{GS}	± 20	V	
Gate-to-Source Voltage	Q2				
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	Q1	$T_A = 25^\circ\text{C}$	8.3	A
			$T_A = 85^\circ\text{C}$	6.0	
		Q2	$T_A = 25^\circ\text{C}$	9.6	
			$T_A = 85^\circ\text{C}$	6.9	
Power Dissipation $R_{\theta JA}$ (Note 1)	Steady State	Q1	$T_A = 25^\circ\text{C}$	1.82	W
			Q2	1.88	
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)	Steady State	Q1	$T_A = 25^\circ\text{C}$	11	A
			$T_A = 85^\circ\text{C}$	8	
		Q2	$T_A = 25^\circ\text{C}$	13	
			$T_A = 85^\circ\text{C}$	9.1	
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)	Steady State	Q1	$T_A = 25^\circ\text{C}$	3.23	W
			Q2	3.27	
Continuous Drain Current $R_{\theta JA}$ (Note 2)	Steady State	Q1	$T_A = 25^\circ\text{C}$	5.5	A
			$T_A = 85^\circ\text{C}$	4.0	
		Q2	$T_A = 25^\circ\text{C}$	6.3	
			$T_A = 85^\circ\text{C}$	4.5	
Power Dissipation $R_{\theta JA}$ (Note 2)	Steady State	Q1	$T_A = 25^\circ\text{C}$	0.80	W
			Q2	0.81	
Pulsed Drain Current	Steady State	Q1	$T_A = 25^\circ\text{C}$ $t_p = 10 \mu\text{s}$	65	A
			Q2	70	
Operating Junction and Storage Temperature	Q1	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	
	Q2				
Source Current (Body Diode)	Q1	I_S	4.2	A	
	Q2				6.0
Drain to Source DV/DT		dV/dt	6	V/ns	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 9.0$ A _{pk} , $L = 0.3$ mH, $R_G = 25 \Omega$)	Q1	EAS	12	mJ	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 9.5$ A _{pk} , $L = 0.3$ mH, $R_G = 25 \Omega$)	Q2	EAS	13.5	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu
- Surface-mounted on FR4 board using the minimum recommended pad size of 90 mm²

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	Q1	R _{θJA}	68.8	°C/W
	Q2		66.4	
Junction-to-Ambient – Steady State (Note 4)	Q1	R _{θJA}	156.4	
	Q2		153.9	
Junction-to-Ambient – (t ≤ 10 s) (Note 3)	Q1	R _{θJA}	38.7	
	Q2		38.2	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu

4. Surface-mounted on FR4 board using the minimum recommended pad size of 90 mm²

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Break-down Voltage	Q1	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
	Q2			30			
Drain-to-Source Break-down Voltage Temperature Coefficient	Q1	V _{(BR)DSS} / T _J			18		mV / °C
	Q2				15		
Zero Gate Voltage Drain Current	Q1	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1	μA
				T _J = 125°C		10	
	Q2		V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		500	
Gate-to-Source Leakage Current	Q1	I _{GSS}	V _{GS} = 0 V, V _{DS} = ±20 V			±100	nA
	Q2					±100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.2		2.2	V	
	Q2			1.2		2.2		
Negative Threshold Temperature Coefficient	Q1	V _{GS(TH)} / T _J			4.5		mV / °C	
	Q2				4.0			
Drain-to-Source On Resistance	Q1	R _{DS(on)}	V _{GS} = 10 V	I _D = 9 A		14	17.4	mΩ
			V _{GS} = 4.5 V	I _D = 9 A		20	25	
	Q2		V _{GS} = 10 V	I _D = 11 A		11	13.3	
			V _{GS} = 4.5 V	I _D = 11 A		16	20	
Forward Transconductance	Q1	g _{FS}	V _{DS} = 1.5 V, I _D = 9 A		16		S	
	Q2				18			

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	Q1	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		605		pF
	Q2				660		
Output Capacitance	Q1	C _{OSS}			190		
	Q2				325		
Reverse Capacitance	Q1	C _{RSS}			102		
	Q2				17.5		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
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CHARGES, CAPACITANCES & GATE RESISTANCE

Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 9 A		6.5		nC		
	Q2				5.0				
Threshold Gate Charge	Q1	Q _{G(TH)}			1.1				
	Q2				1.1				
Gate-to-Source Charge	Q1	Q _{GS}			1.9				
	Q2				2.0				
Gate-to-Drain Charge	Q1	Q _{GD}			3.2				
	Q2				1.46				
Total Gate Charge	Q1	Q _{G(TOT)}		V _{GS} = 10 V, V _{DS} = 15 V; I _D = 9 A		12			nC
	Q2					10.6			

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 9 A, R _G = 3.0 Ω		8.0		ns
	Q2				7.5		
Rise Time	Q1	t _r			7.2		
	Q2				11.2		
Turn-Off Delay Time	Q1	t _{d(OFF)}			11		
	Q2				11.6		
Fall Time	Q1	t _f			3.3		
	Q2				1.9		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 9 A, R _G = 3.0 Ω		4.2		ns
	Q2				4.3		
Rise Time	Q1	t _r			11.6		
	Q2				11.4		
Turn-Off Delay Time	Q1	t _{d(OFF)}			14.1		
	Q2				14.3		
Fall Time	Q1	t _f			2.0		
	Q2				1.3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Voltage	Q1	V _{SD}	V _{GS} = 0 V, I _S = 3 A	T _J = 25°C	0.80	1.2	V
				T _J = 125°C	0.65		
	Q2		V _{GS} = 0 V, I _S = 2 A	T _J = 25°C	0.50	0.80	
				T _J = 125°C	0.45		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	Q1	t _{RR}	V _{GS} = 0 V, d _{IS} /d _t = 100 A/μs, I _S = 3 A		17.9		ns
	Q2				23.3		
Charge Time	Q1	t _a			9.0		
	Q2				11.3		
Discharge Time	Q1	t _b			9.0		
	Q2				12		
Reverse Recovery Charge	Q1	Q _{RR}			8.0		nC
	Q2				12		

PACKAGE PARASITIC VALUES

Source Inductance	Q1	L _S	T _A = 25°C		0.36		nH
	Q2				0.36		
Drain Inductance	Q1	L _D			0.054		nH
	Q2				0.054		
Gate Inductance	Q1	L _G			1.3		nH
	Q2				1.3		
Gate Resistance	Q1	R _G			0.8		Ω
	Q2				0.8		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

6. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTLLD4901NFTWG	WDFN8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – Q1

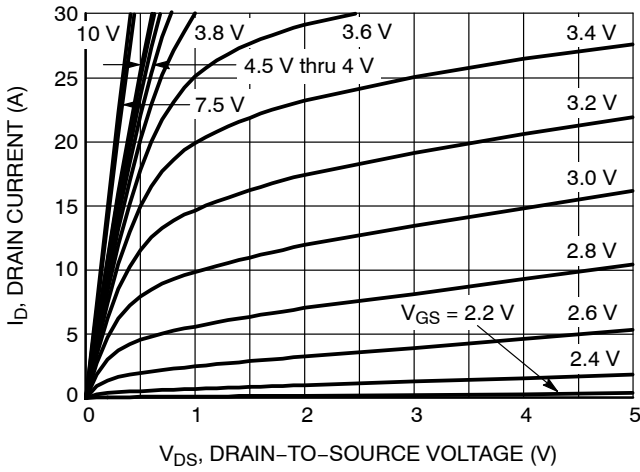


Figure 1. On-Region Characteristics

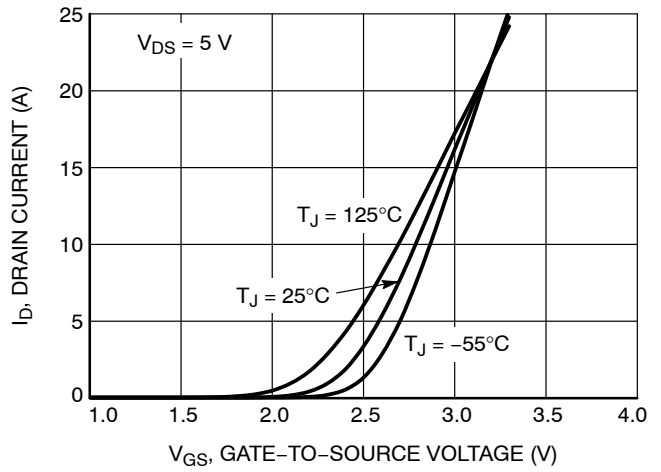


Figure 2. Transfer Characteristics

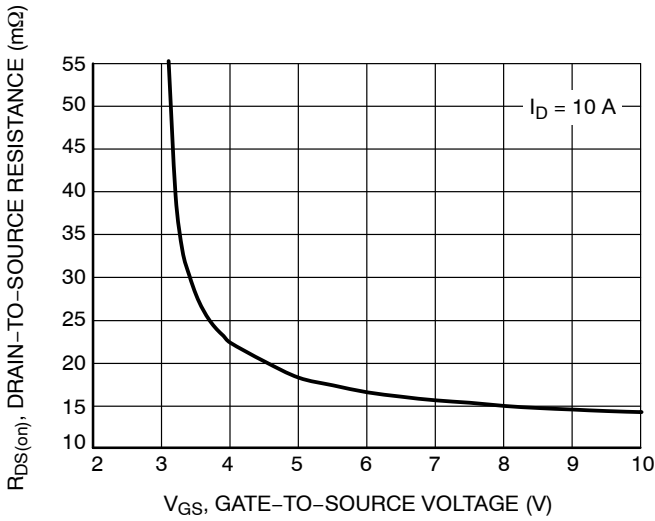


Figure 3. On-Resistance vs. Gate-to-Source Resistance

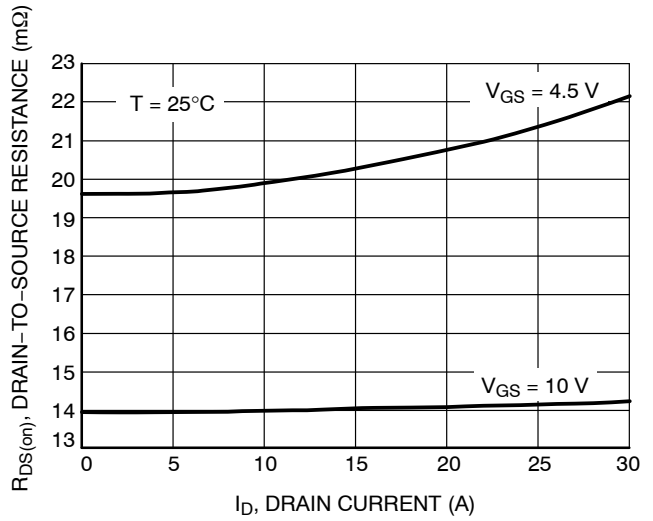


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

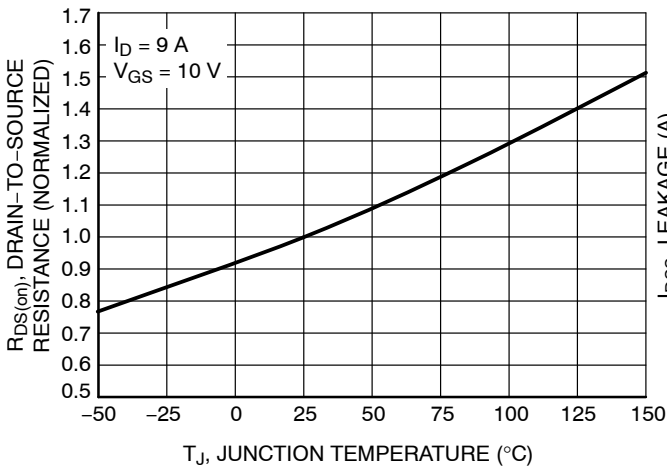


Figure 5. On-Resistance Variation with Temperature

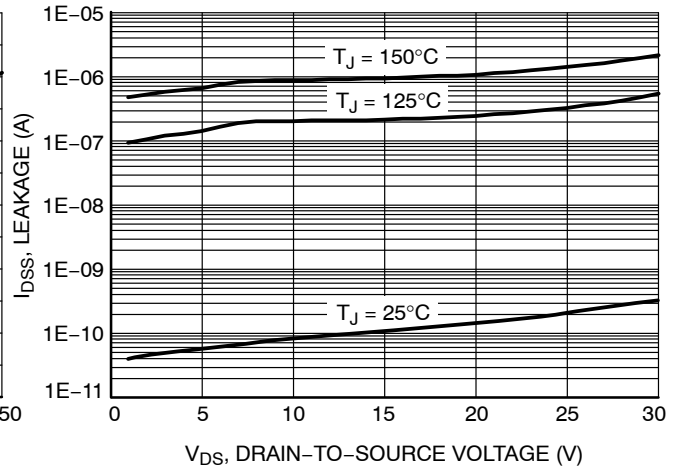


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS – Q1

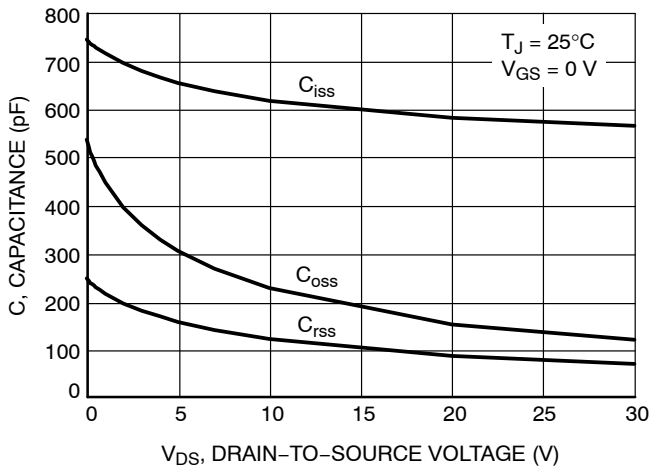


Figure 7. Capacitance Variation

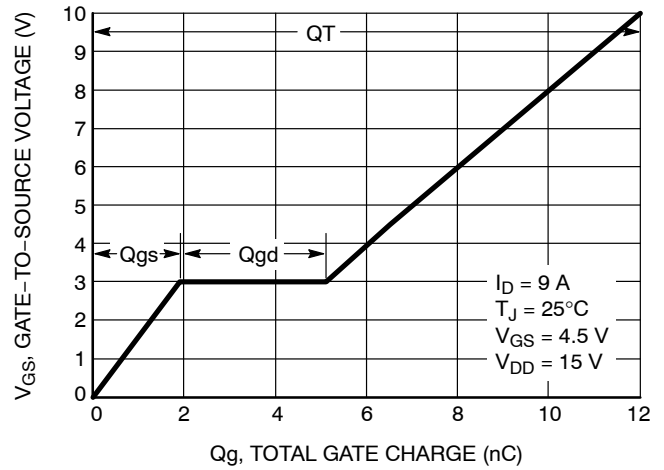


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

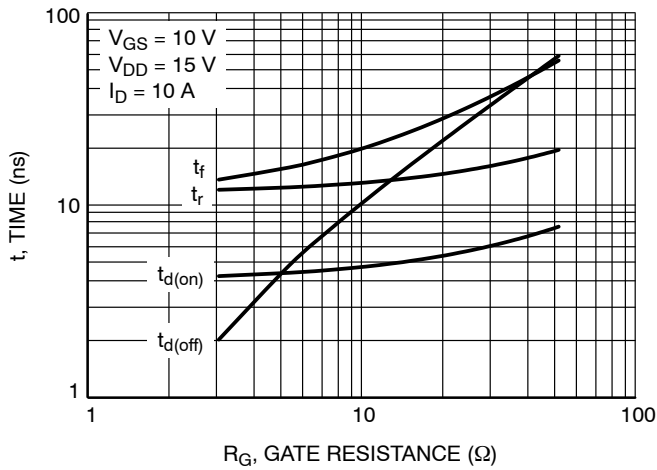


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

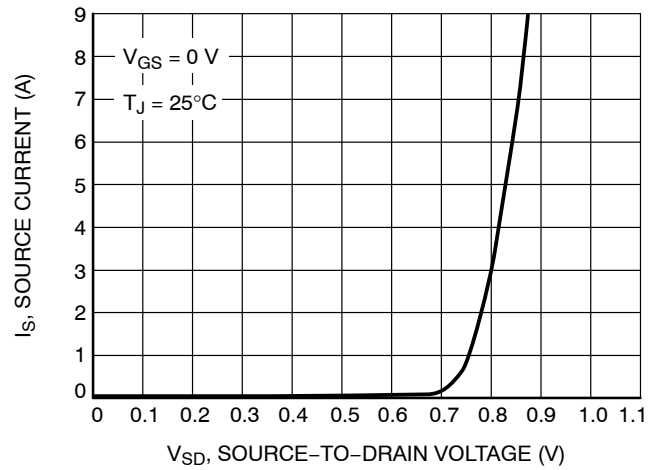


Figure 10. Diode Forward Voltage vs. Current

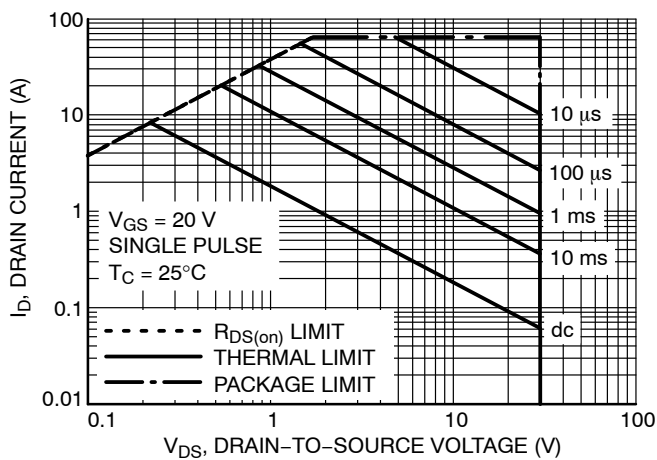


Figure 11. Maximum Rated Forward Biased Safe Operating Area

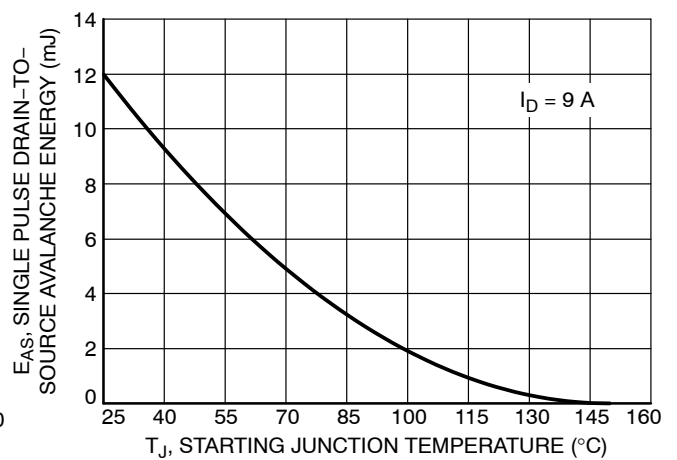


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS – Q1

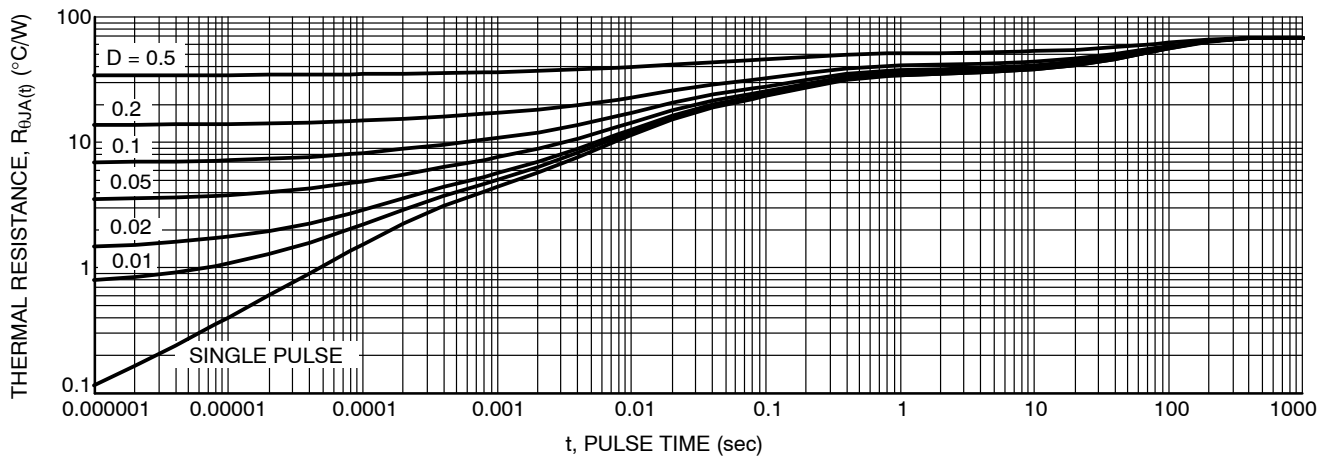


Figure 13. Thermal Response

TYPICAL CHARACTERISTICS – Q2

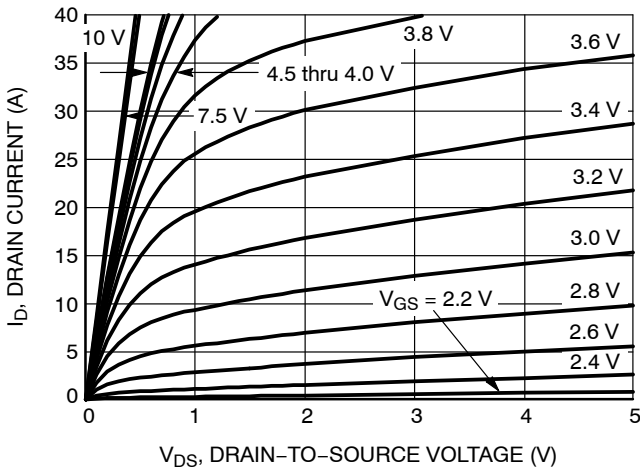


Figure 14. On-Region Characteristics

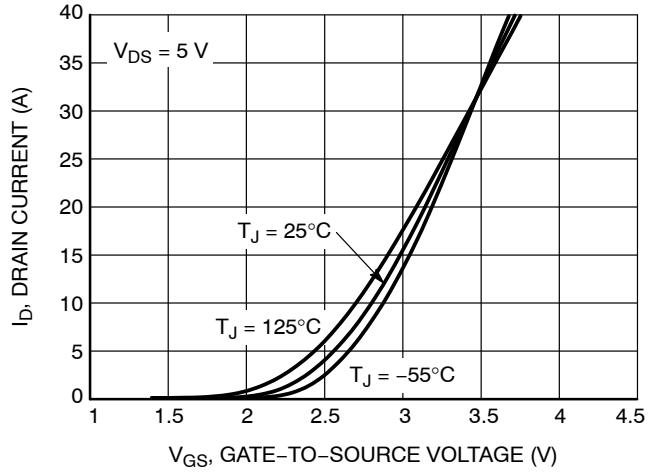


Figure 15. Transfer Characteristics

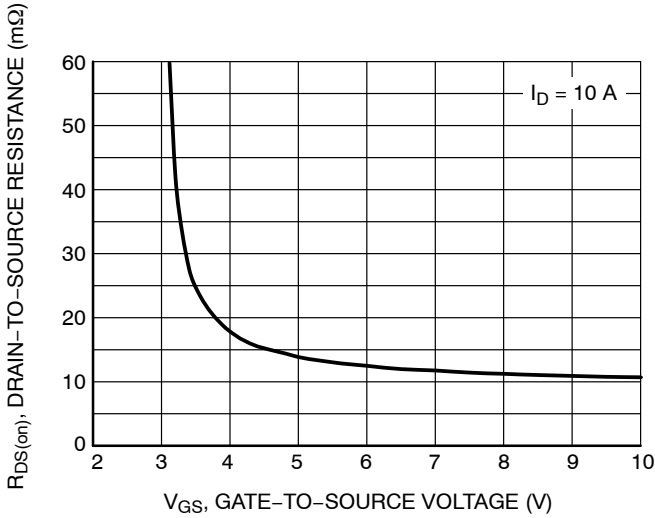


Figure 16. On-Resistance vs. Gate-to-Source Resistance

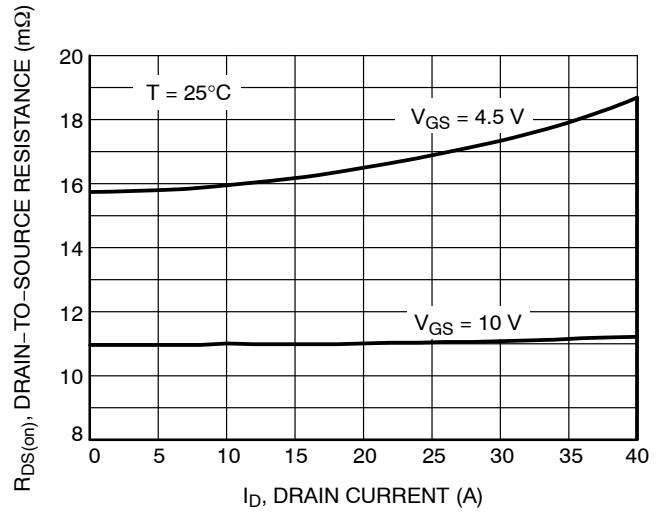


Figure 17. On-Resistance vs. Drain Current and Gate Voltage

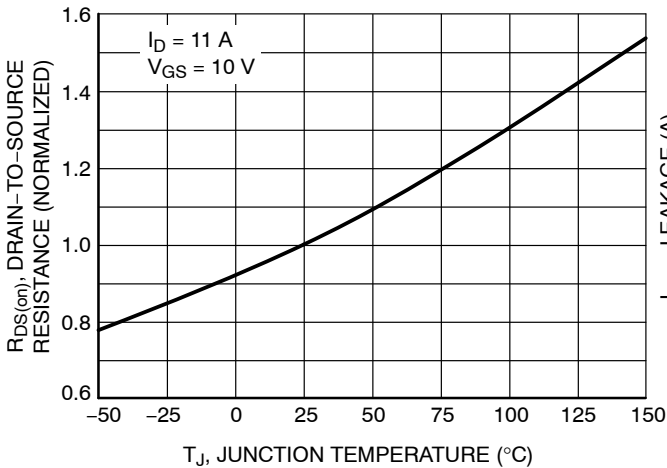


Figure 18. On-Resistance Variation with Temperature

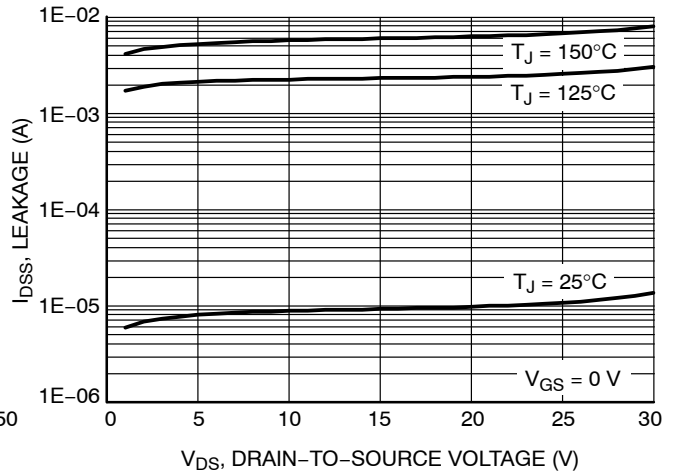


Figure 19. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS – Q2

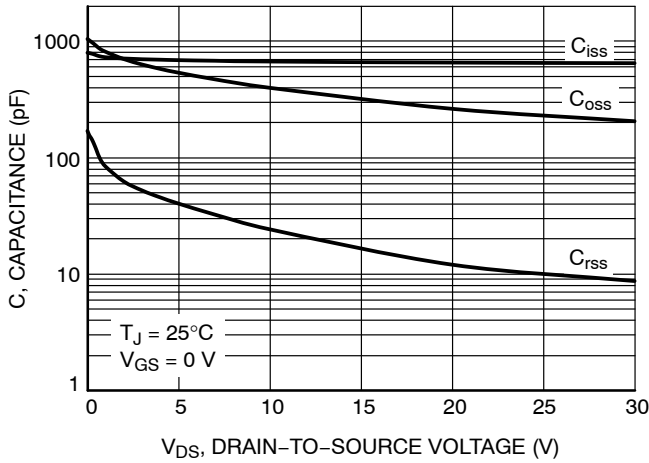


Figure 20. Capacitance Variation

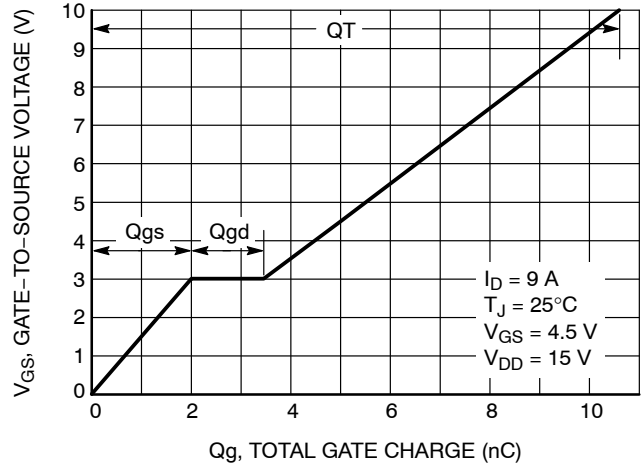


Figure 21. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

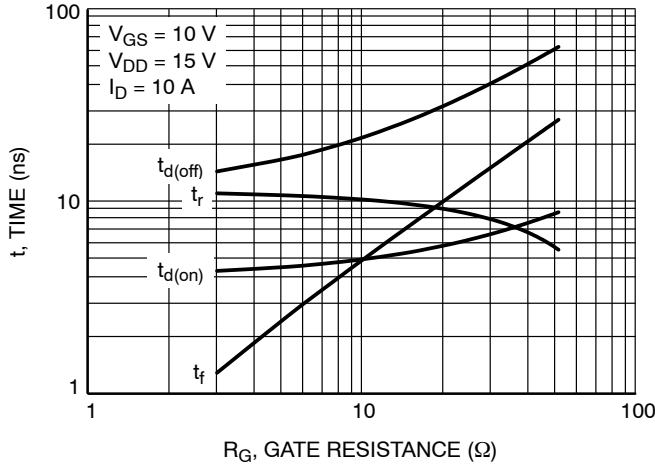


Figure 22. Resistive Switching Time Variation vs. Gate Resistance

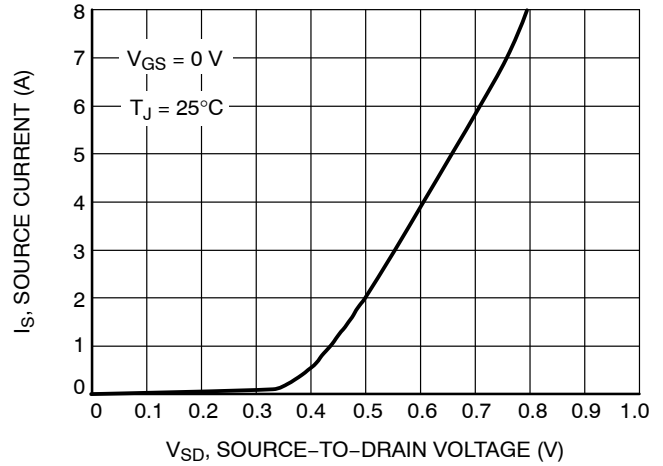


Figure 23. Diode Forward Voltage vs. Current

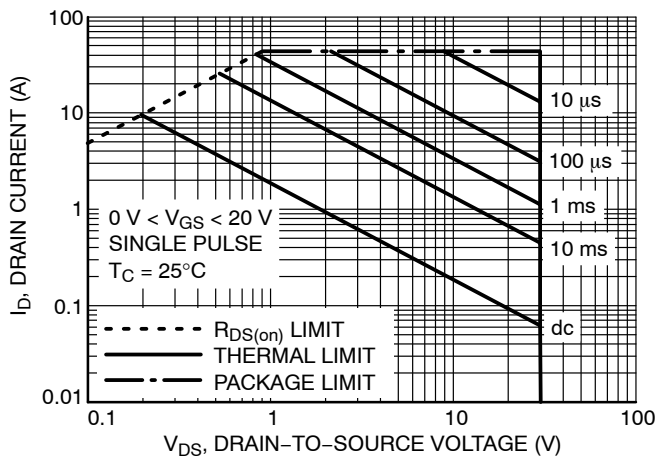


Figure 24. Maximum Rated Forward Biased Safe Operating Area

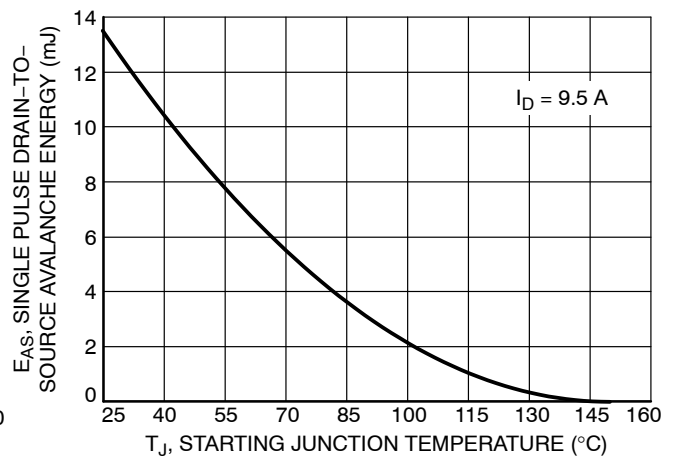


Figure 25. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS – Q2

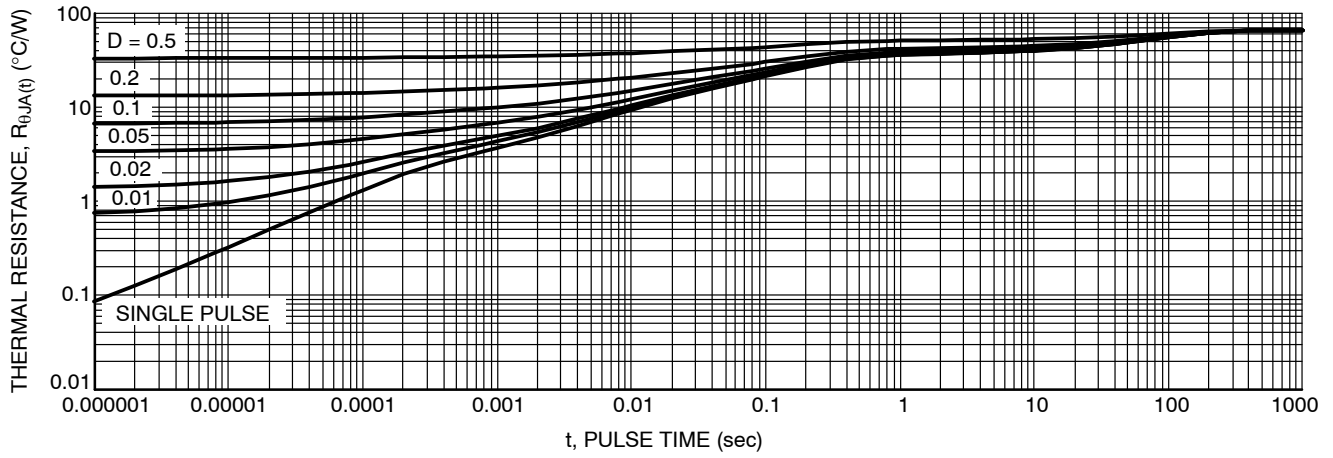


Figure 26. Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

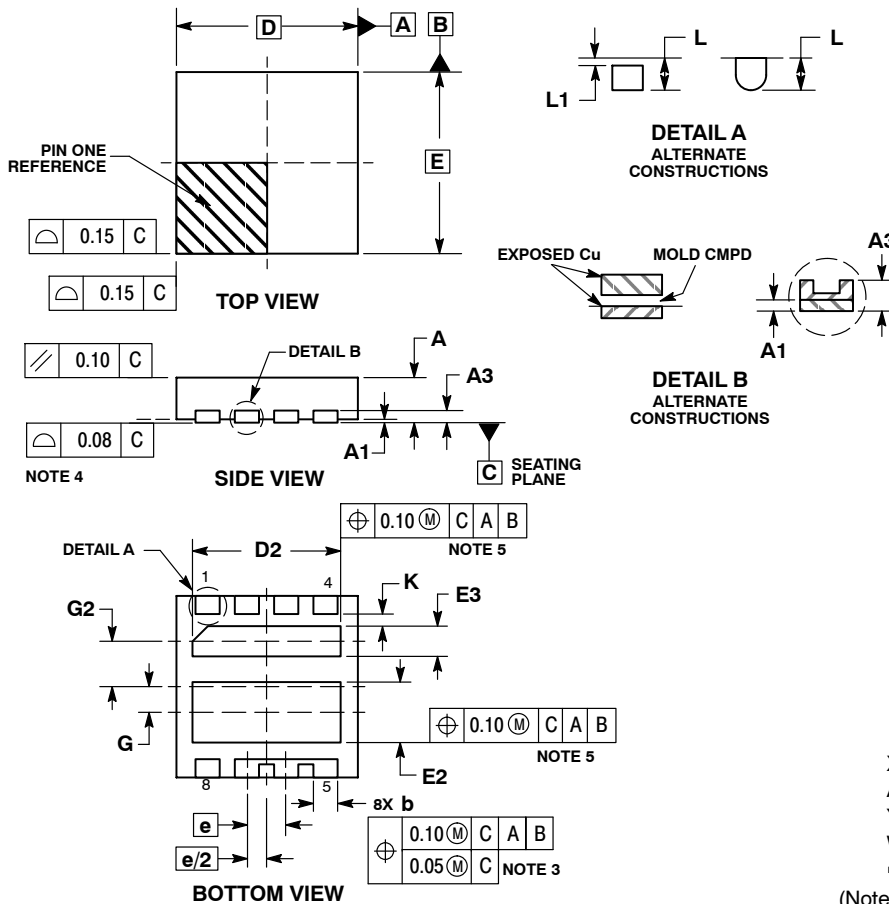
ON Semiconductor®



SCALE 2:1

WDFN8 3x3, 0.65P
CASE 511BP
ISSUE B

DATE 17 JUL 2012

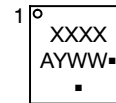


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.05 AND 0.15 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. POSITIONAL TOLERANCE APPLIES TO ALL OF THE EXPOSED PADS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20	REF
b	0.30	0.50
D	3.00	BSC
D2	2.35	2.55
E	3.00	BSC
E2	0.90	1.10
E3	0.40	0.60
e	0.65	BSC
G	0.43	BSC
G2	0.68	BSC
K	0.20	---
L	0.20	0.40
L1	0.00	0.15

GENERIC MARKING DIAGRAM*

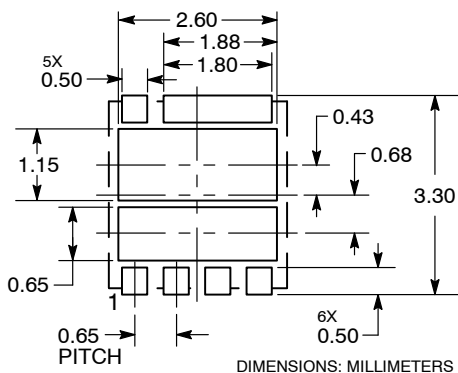


- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



- STYLE 1:**
1. GATE 1
 2. DRAIN 1
 3. DRAIN 1
 4. DRAIN 1
 5. SOURCE 2
 6. SOURCE 2
 7. SOURCE 2
 8. GATE 2
 9. DRAIN 1
 10. SOURCE 1/DRAIN 2

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	WDFN8, 3X3, 0.65P	PAGE 1 OF 1

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